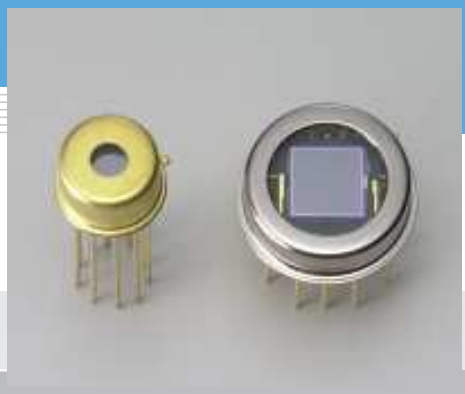


# Si photodiode with preamp S8745-01, S8746-01

Photodiode and preamp integrated with feedback resistance and capacitance



S8745-01, S8746-01 are low-noise sensors consisting of Si photodiode, op amp, and feedback resistance and capacitance, all integrated into a small package. By simply connecting to a power supply, S8745-01 and S8746-01 can be used in low-light-level measurement such as analytical equipment and measurement equipment. The active area of the photodiode is internally connected to the GND terminal making it highly resistant to EMC noise.

## Features

- Si photodiode for UV to near IR precision photometry
- Small metal package with quartz window  
S8745-01: TO-5  
S8746-01: TO-8
- Active area  
S8745-01: 2.4 × 2.4 mm  
S8746-01: 5.8 × 5.8 mm
- FET input operational amplifier with low power dissipation
- Built-in  $R_f=1\text{ G}\Omega$  and  $C_f=5\text{ pF}$
- Variable gain with an externally connected resistor
- Low noise and NEP
- Package with shielding effect
- Resistant to EMC noise

## Applications

- Spectrophotometry
- General-purpose optical measurement

S8745-01, S8746-01 may be damaged by Electro Static Discharge, etc. Please see Precautions for use in the last page.

### Absolute maximum ratings ( $T_a=25\text{ }^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Supply voltage (op amp)	$V_{cc}$	$\pm 20$	V
Power dissipation	P	500	mW
Operating temperature	$T_{opr}$	-20 to +60	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-30 to +80	$^\circ\text{C}$

### Electrical and optical characteristics (Typ. $T_a=25\text{ }^\circ\text{C}$ , $V_{cc}=\pm 15\text{ V}$ , $R_L=1\text{ M}\Omega$ , unless otherwise noted)

Parameter	Symbol	Condition	S8745-01	S8746-01	Unit
Spectral response range	$\lambda$		190 to 1100		nm
Peak sensitivity wavelength	$\lambda_p$		960		nm
Feedback resistance (built-in)	Rf		1		G $\Omega$
Feedback capacitance (built-in)	Cf		5		pF
Photo sensitivity	S	$\lambda$ =200 nm	0.12		V/nW
		$\lambda$ = $\lambda_p$	0.52		
Output noise voltage	Vn	Dark state f=10 Hz	6	7	$\mu$ Vrms/Hz <sup>1/2</sup>
		Dark state, f=20 Hz	5	6	
Noise equivalent power	NEP	$\lambda$ = $\lambda_p$ , f=10 Hz	11	15	fW/Hz <sup>1/2</sup>
		$\lambda$ = $\lambda_p$ , f=20 Hz	11	15	
Output offset voltage	Vos	Dark state	$\pm$ 4		mV
Cut-off frequency	fc	-3 dB	32		Hz
Output voltage swing	Vo		13		V
Supply current	Icc	Dark state	0.3		mA